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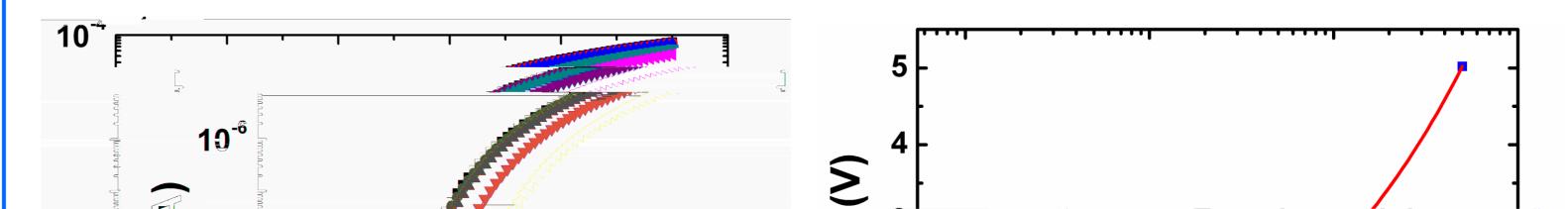
Amorphous oxide semiconductors (AOSs) are emerging as promising materials for the active layers of thin film transistors (TFTs), which are used in active-matrix liquid crystal display (AMLCD) and active

Experimental

The channel layer deposition:

- ➢ Via PLD (10Hz; 300 mJ)
- Ceramic target
- Room temperature
- ➢ Oxygen partial pressure: 6.7 Pa
- Substrate-target distance: 4.5 ~ 6 cm

B. Stability of annealed *a***-InGaZnO TFTs**



Thickness: 50 nm

➤ Annealing at 400 °C in air

Fig. 2. Schematic of an *a*-InGaZnO TFT in a bottomgate coplanar configuration.

Results and discussion

